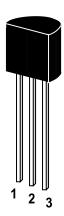
NPN Silicon Epitaxial Planar Transistor

Audio Frequency Power amplifier applications.

The transistor is subdivided into three group, O, Y and G according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25°C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I _C	1	Α
Power Dissipation	P _{tot}	1	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







ST 2SD471

Characteristics at T_{amb}=25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V_{CE} =1V, I_{C} =100mA						
Current Gain Group	0	h_{FE}	70	-	140	-
	Υ	h_{FE}	120	-	240	-
	G	h _{FE}	200	-	400	-
Collector Emitter Breakdown Voltage						
at I _C =10mA		$V_{(BR)CEO}$	30	-	-	V
Collector Base Breakdown Voltage						
at $I_C=100\mu A$		$V_{(BR)CBO}$	40	-	-	V
Emitter Base Breakdown Voltage						
at I _E =100μA		$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current						
at V _{CB} =30V		I_{CBO}	-	-	0.1	μΑ
Collector Saturation Voltage						
at I _C =1.0A, I _B =100mA		$V_{CE(sat)}$	-	-	0.5	V
Base Saturation Voltage						
at I _C =1.0A, I _B =100mA		$V_{BE(sat)}$	-	-	1.2	V
Collector Output Capacitance						
at V _{CB} =6V, f=1MHz		C_OB	-	18	-	pF
Transition Frequency						
at V _{CE} =6V, I _C =10mA		f_T	-	130	-	MHz







